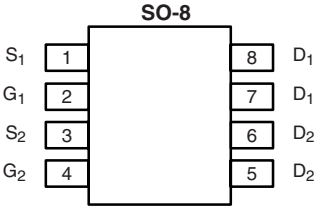
N- and P-Channel 40-V (D-S) MOSFET

PRODUCT SUMMARY				
	V_{DS} (V)	$R_{DS(on)}$ (Ω)	I_D (A)[a]	Q_g (Typ.)
N-Channel	40	0.0355 at V_{GS} = 10 V	6.8	5.3
		0.0425 at V_{GS} = 4.5 V	6.2	
P-Channel	- 40	0.035 at V_{GS} = - 10 V	- 7.2	17
		0.047 at V_{GS} = - 4.5 V	- 6.2	

SO-8



Top View

Ordering Information: Si4561DY-T1-E3 (Lead (Pb)-free)
Si4561DY-T1-GE3 (Lead (Pb)-free and Halogen-free)

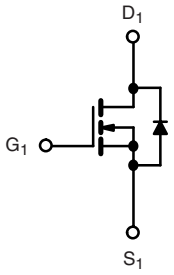
FEATURES

- **Halogen-free According to IEC 61249-2-21 Available**
- TrenchFET® Power MOSFET

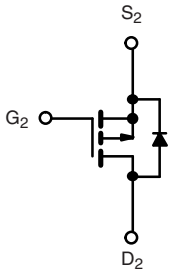
Pb-free
RoHS COMPLIANT
HALOGEN FREE Available

APPLICATIONS

- Backlight Inverter for LCD Display



N-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS T_A = 25 °C, unless otherwise noted

Parameter		Symbol	N-Channel	P-Channel	Unit
Drain-Source Voltage		V_{DS}	40	- 40	V
Gate-Source Voltage		V_{GS}	± 20		
Continuous Drain Current (T_J = 150 °C)	T_C = 25 °C	I_D	6.8	- 7.2	A
	T_C = 70 °C		5.4	- 5.7	
	T_A = 25 °C		5.6[b, c]	- 5.6[b, c]	
	T_A = 70 °C		4.4[b, c]	- 4.4[b, c]	
Pulsed Drain Current		I_{DM}	20	- 20	
Source-Drain Current Diode Current	T_C = 25 °C	I_S	2.5	- 2.5	
	T_A = 25 °C		1.6[b, c]	- 1.6[b, c]	
Pulsed Source-Drain Current		I_{SM}	20	- 20	
Single Pulse Avalanche Current	L = 0 1 mH	I_{AS}	7	15	
Single Pulse Avalanche Energy		E_{AS}	2.45	11.25	mJ
Maximum Power Dissipation	T_C = 25 °C	P_D	3.0	3.3	W
	T_C = 70 °C		1.9	2.10	
	T_A = 25 °C		2.0[b, c]	2.0[b, c]	
	T_A = 70 °C		1.25[b, c]	1.25[b, c]	
Operating Junction and Storage Temperature Range		T_J, T_{stg}	- 55 to 150		°C

THERMAL RESISTANCE RATINGS

Parameter		Symbol	N-Channel		P-Channel		Unit
			Typ.	Max.	Typ.	Max.	
Maximum Junction-to-Ambient[b, d]	t ≤ 10 s	R_{thJA}	54	64	50	62.5	°C/W
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	33	42	31	37	

Notes:
a. Based on T_C = 25 °C.
b. Surface Mounted on 1" x 1" FR4 board.
c. t = 10 s.
d. Maximum under Steady State conditions is 120 °C/W.

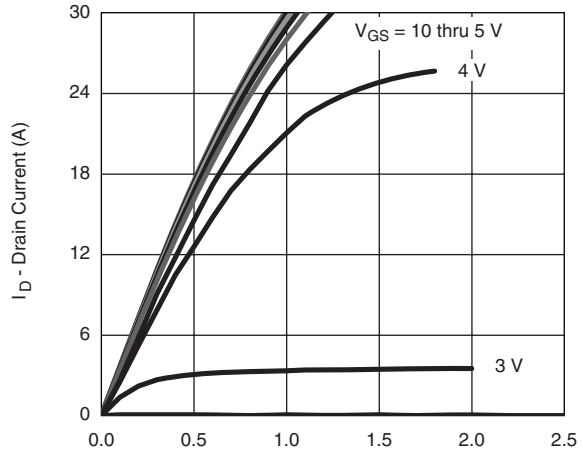
SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
Parameter	**Symbol**	**Test Conditions**		**Min.**	**Typ.[a]**	**Max.**	**Unit**
Static							
Drain-Source Breakdown Voltage	V_{DS}	V_{GS} = 0 V, I_D = 250 µA	N-Ch	40			V
		V_{GS} = 0 V, I_D = - 250 µA	P-Ch	- 40			
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	I_D = 250 µA	N-Ch		44		mV/°C
		I_D = - 250 µA	P-Ch		- 41		
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$	I_D = 250 µA	N-Ch		- 5.5		
		II_D = - 250 µA	P-Ch		4.3		
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS}, I_D = 250 µA	N-Ch	1.4		3.0	V
		V_{DS} = V_{GS}, I_D = - 250 µA	P-Ch	- 1.4		- 3.0	
Gate-Body Leakage	I_{GSS}	V_{DS} = 0 V, V_{GS} = ± 20 V	N-Ch			100	nA
			P-Ch			- 100	
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40 V, V_{GS} = 0 V	N-Ch			1	µA
		V_{DS} = - 40 V, V_{GS} = 0 V	P-Ch			- 1	
		V_{DS} = 40 V, V_{GS} = 0 V, T_J = 55 °C	N-Ch			10	
		V_{DS} = - 40 V, V_{GS} = 0 V, T_J = 55 °C	P-Ch			- 10	
On-State Drain Current[b]	$I_{D(on)}$	V_{DS} = 5 V, V_{GS} = 10 V	N-Ch	10			A
		V_{DS} = - 5 V, V_{GS} = - 10 V	P-Ch	- 10			
Drain-Source On-State Resistance[b]	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 5 A	N-Ch		0.0295	0.0355	Ω
		V_{GS} = - 10 V, I_D = - 5 A	P-Ch		0.0285	0.035	
		V_{GS} = 4.5 V, I_D = 4 A	N-Ch		0.0355	0.0425	
		V_{GS} = - 4.5 V, I_D = - 4 A	P-Ch		0.037	0.047	
Forward Transconductance[b]	g_{fs}	V_{DS} = 15 V, I_D = 5 A	N-Ch		22		S
		V_{DS} = - 15 V, I_D = - 5 A	P-Ch		20		
Dynamic[a]							
Input Capacitance	C_{iss}	N-Channel V_{DS} = 20 V, V_{GS} = 0 V, f = 1 MHz	N-Ch		640		pF
			P-Ch		1555		
Output Capacitance	C_{oss}		N-Ch		73		
		P-Channel V_{DS} = - 20 V, V_{GS} = 0 V, f = 1 MHz	P-Ch		176		
Reverse Transfer Capacitance	C_{rss}		N-Ch		41		
			P-Ch		142		
Total Gate Charge	Q_g	V_{DS} = 20 V, V_{GS} = 10 V, I_D = 5 A	N-Ch		11.7	20	nC
		V_{DS} = - 20 V, V_{GS} = - 10 V, I_D = - 5 A	P-Ch		38.5	60	
		N-Channel V_{DS} = 20 V, V_{GS} = 4.5 V I_D = 5 A	N-Ch		5.3	9	
			P-Ch		17	27	
Gate-Source Charge	Q_{gs}		N-Ch		1.9		
		P-Channel V_{DS} = - 20 V, V_{GS} = - 4.5 V, I_D = - 5 A	P-Ch		4.2		
Gate-Drain Charge	Q_{gd}		N-Ch		1.7		
			P-Ch		7.0		
Gate Resistance	R_g	f = 1 MHz	N-Ch		2.2		Ω
			P-Ch		3		

SPECIFICATIONS T_J = 25 °C, unless otherwise noted							
Parameter	**Symbol**	**Test Conditions**		**Min.**	**Typ.[a]**	**Max.**	**Unit**
Dynamic[a]							
Turn-On Delay Time	$t_{d(on)}$	N-Channel V_{DD} = 20 V, R_L = 4 Ω $I_D \cong$ 5 A, V_{GEN} = 10 V, R_g = 1 Ω	N-Ch		7	14	ns
			P-Ch		11	20	
Rise Time	t_r		N-Ch		10	20	
			P-Ch		15	30	
Turn-Off Delay Time	$t_{d(off)}$	P-Channel V_{DD} = - 20 V, R_L = 4 Ω $I_D \cong$ - 5 A, V_{GEN} = - 10 V, R_g = 1 Ω	N-Ch		15	30	
			P-Ch		36	60	
Fall Time	t_f		N-Ch		9	18	
			P-Ch		9	18	
Turn-On Delay Time	$t_{d(on)}$	N-Channel V_{DD} = 20 V, R_L = 4 Ω $I_D \cong$ 5 A, V_{GEN} = 4.5 V, R_g = 1 Ω	N-Ch		16	30	
			P-Ch		49	80	
Rise Time	t_r		N-Ch		17	30	
			P-Ch		79	120	
Turn-Off Delay Time	$t_{d(off)}$	P-Channel V_{DD} = - 20 V, R_L = 4 Ω $I_D \cong$ - 5 A, V_{GEN} = - 4.5 V, R_g = 16 Ω	N-Ch		16	30	
			P-Ch		35	60	
Fall Time	t_f		N-Ch		10	20	
			P-Ch		14	25	
Drain-Source Body Diode Characteristics							
Continuous Source-Drain Diode Current	I_S	T_C = 25 °C	N-Ch			2.5	A
			P-Ch			- 2.5	
Pulse Diode Forward Current[a]	I_{SM}		N-Ch			20	
			P-Ch			- 20	
Body Diode Voltage	V_{SD}	I_S = 1.6 A	N-Ch		0.78	1.2	V
		I_S = - 1.6 A	P-Ch		- 0.74	- 1.2	
Body Diode Reverse Recovery Time	t_{rr}	N-Channel I_F = 2 A, dI/dt = 100 A/µs, T_J = 25 °C P-Channel I_F = - 2 A, dI/dt = - 100 A/µs, T_J = 25 °C	N-Ch		19	30	ns
			P-Ch		22	40	
Body Diode Reverse Recovery Charge	Q_{rr}		N-Ch		14	25	nC
			P-Ch		22	35	
Reverse Recovery Fall Time	t_a		N-Ch		13		ns
			P-Ch		15		
Reverse Recovery Rise Time	t_b		N-Ch		6		
			P-Ch		7		

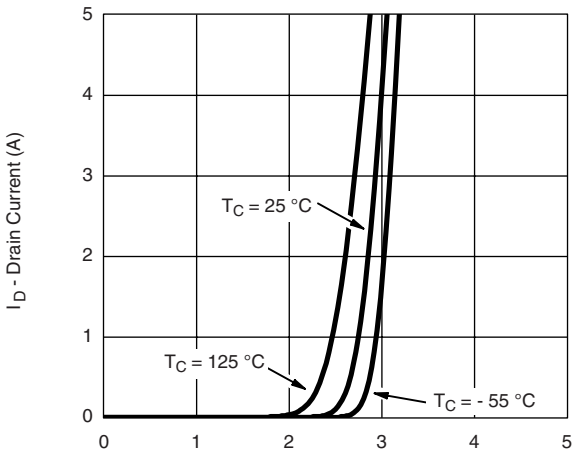
Notes:
a. Guaranteed by design, not subject to production testing.
b. Pulse test; pulse width ≤ 300 µs, duty cycle ≤ 2 %.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

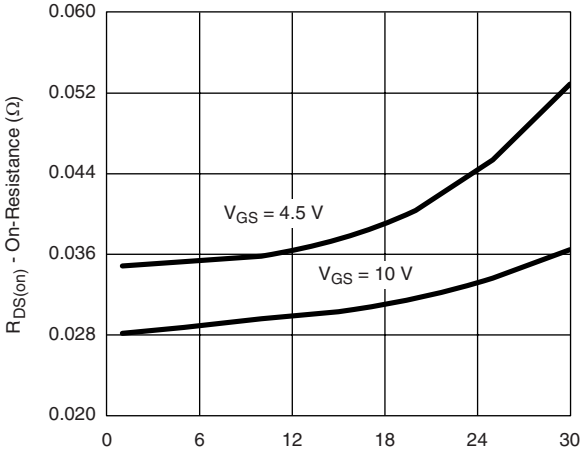
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



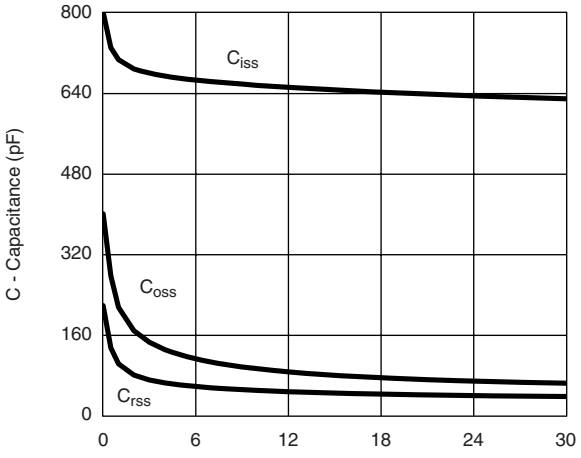
Output Characteristics



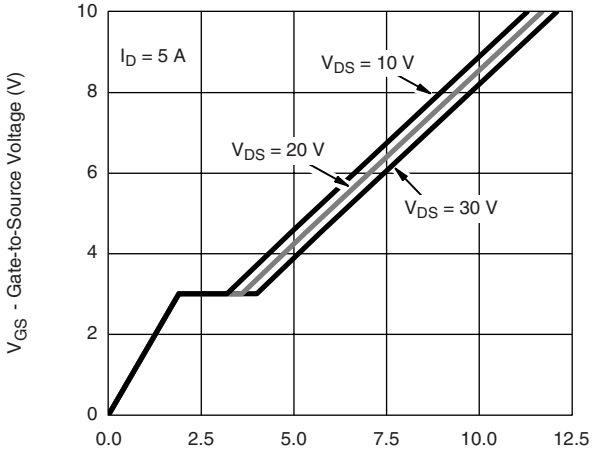
Transfer Characteristics



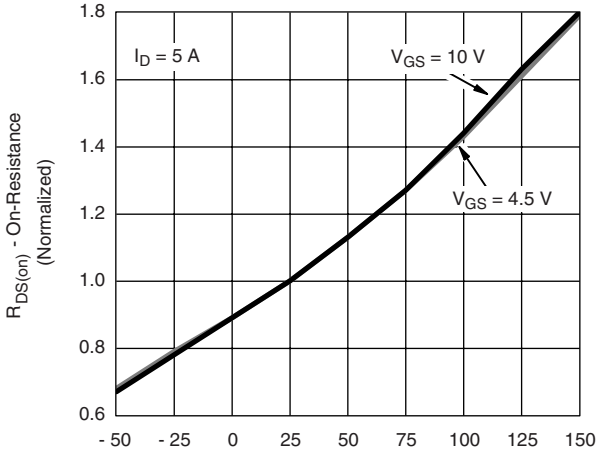
On-Resistance vs. Drain Current



Capacitance

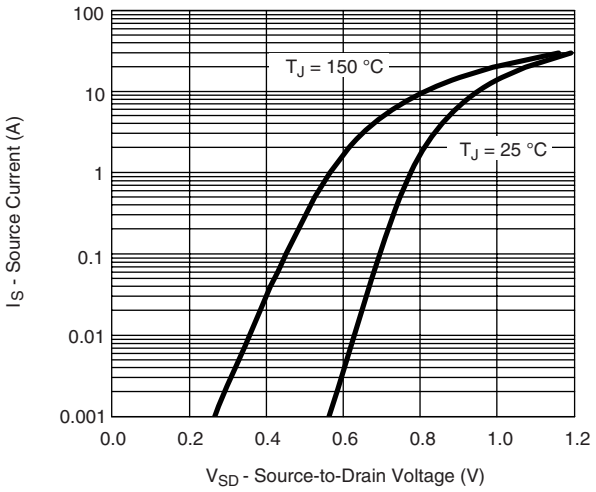


Gate Charge

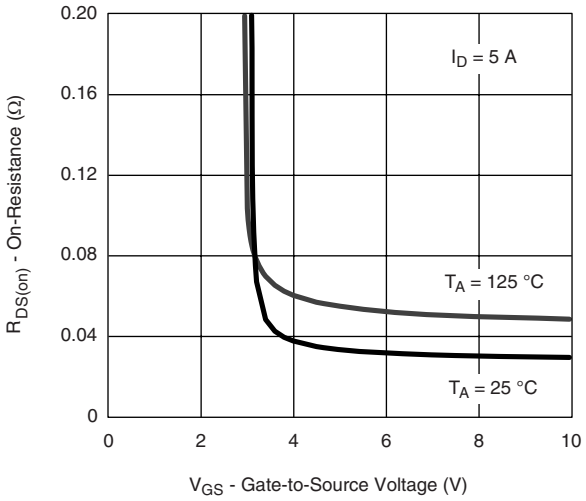


On-Resistance vs. Junction Temperature

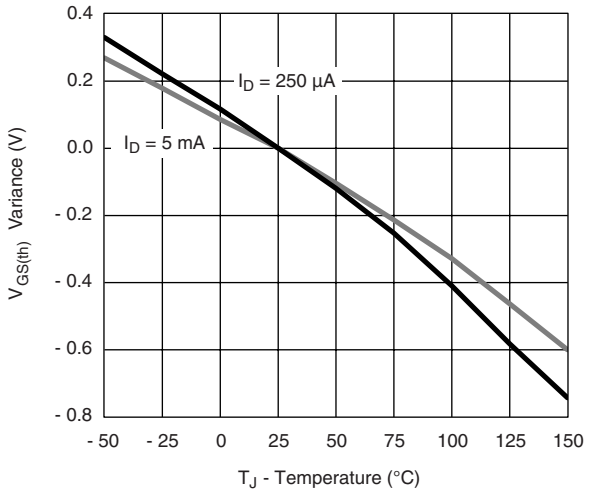
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



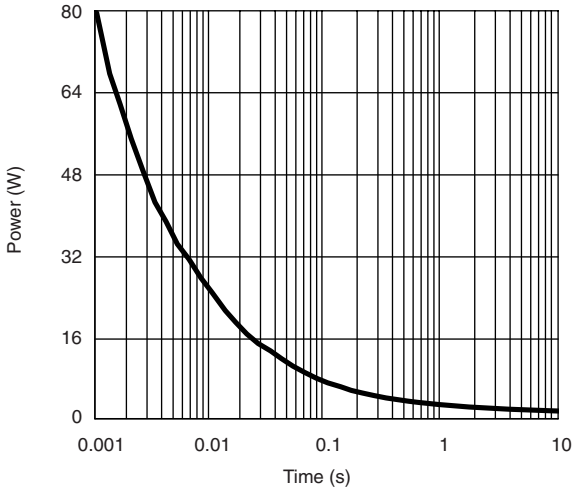
Source-Drain Diode Forward Voltage



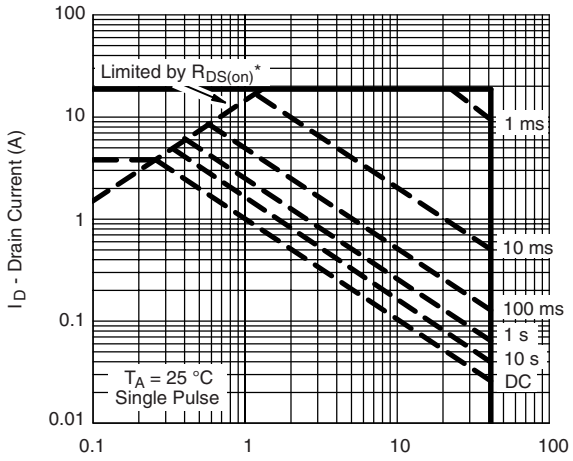
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



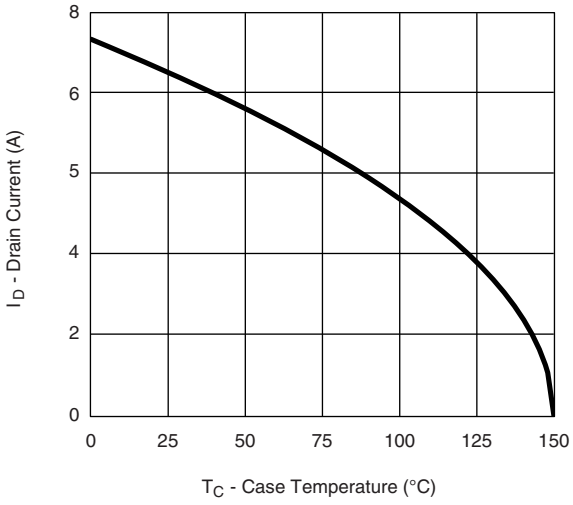
Single Pulse Power, Junction-to-Ambient



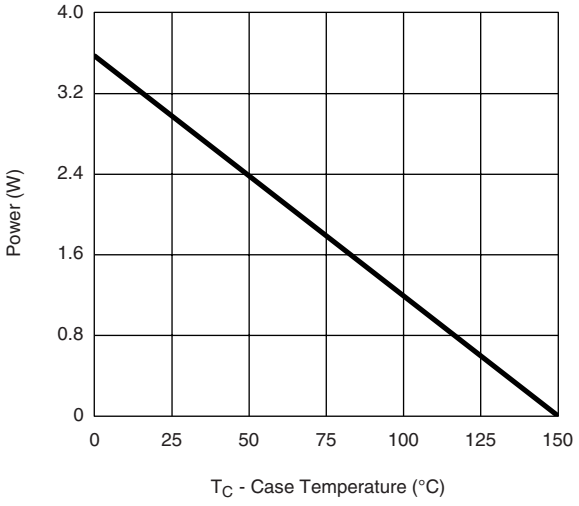
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

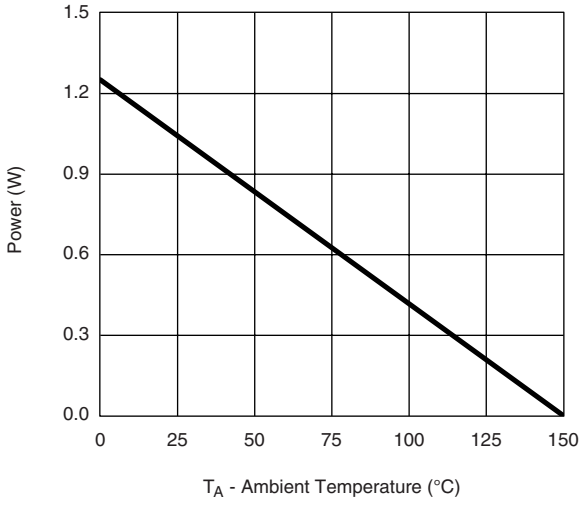
N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



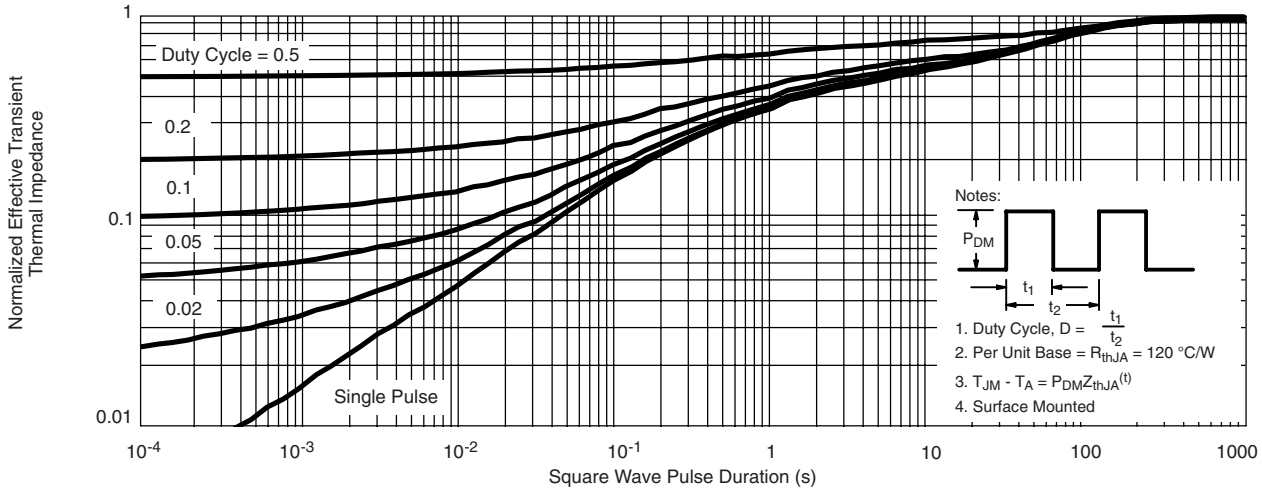
Power Derating, Junction-to-Foot



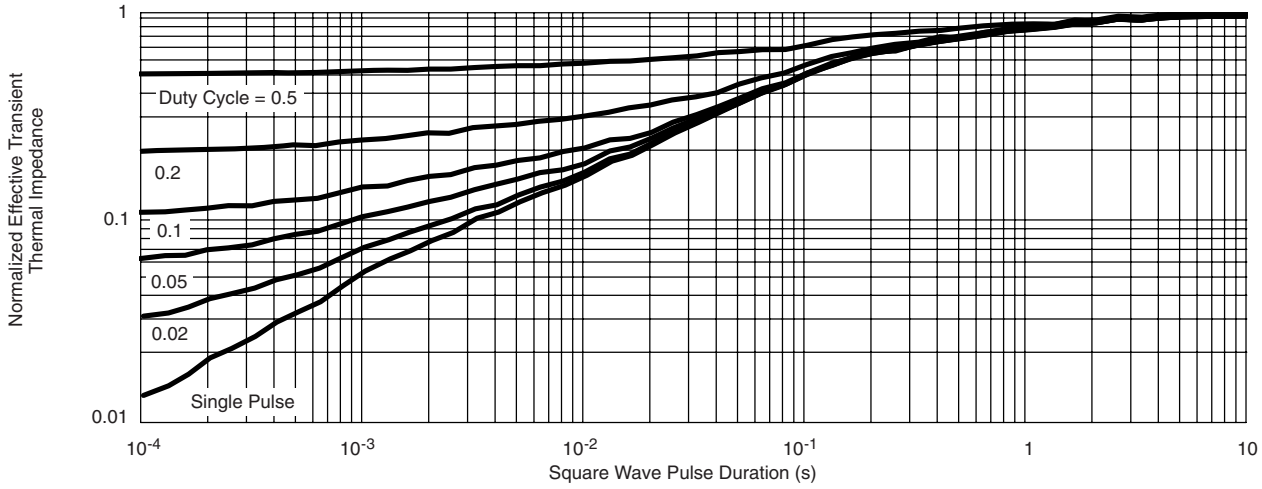
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

N-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

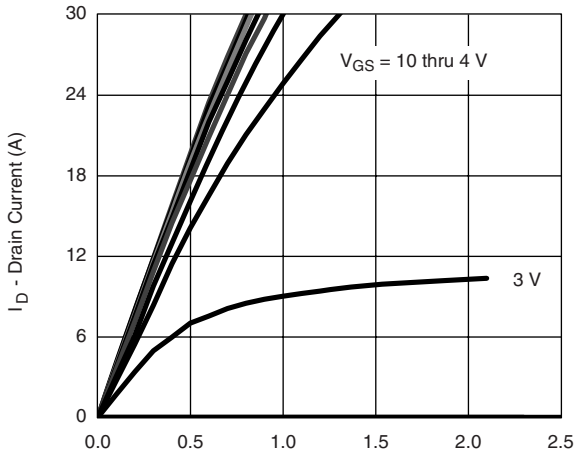


Normalized Thermal Transient Impedance, Junction-to-Ambient

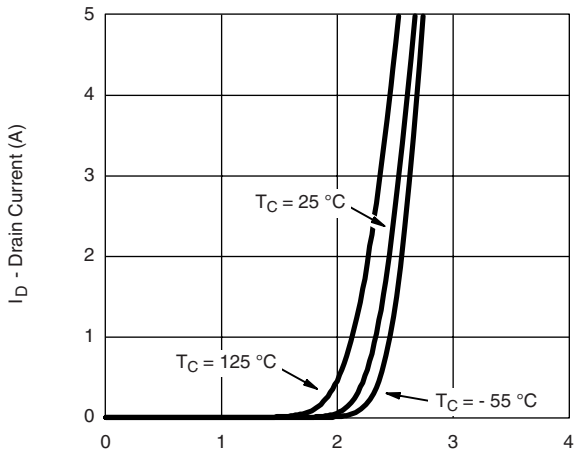


Normalized Thermal Transient Impedance, Junction-to-Foot

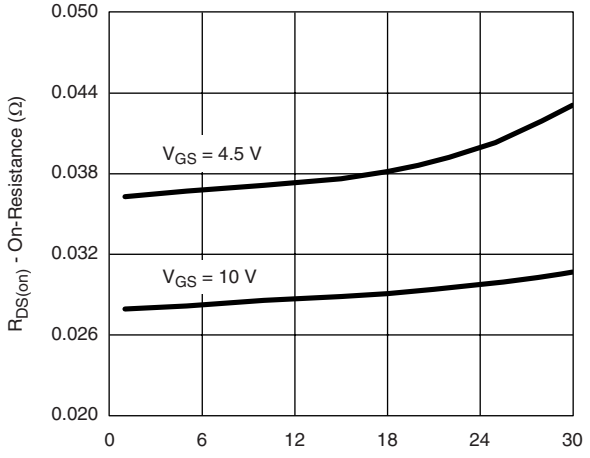
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



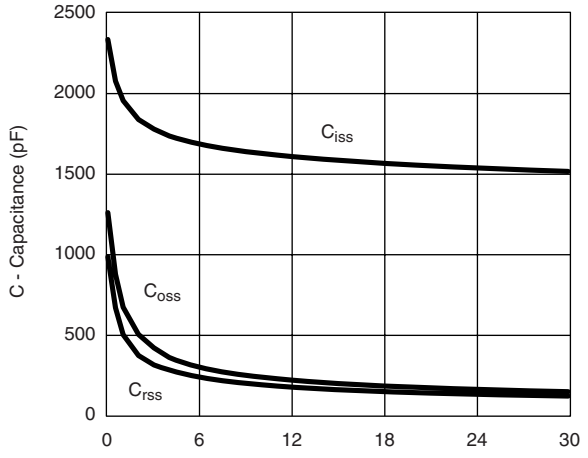
Output Characteristics



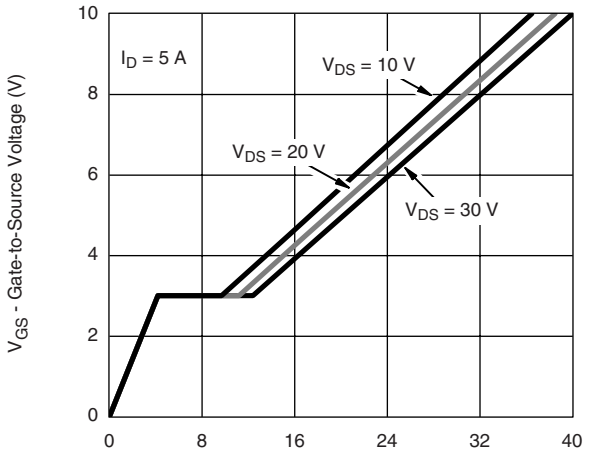
Transfer Characteristics



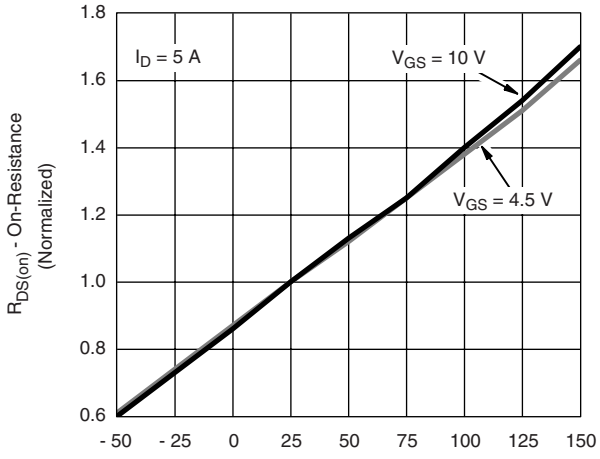
On-Resistance vs. Drain Current



Capacitance

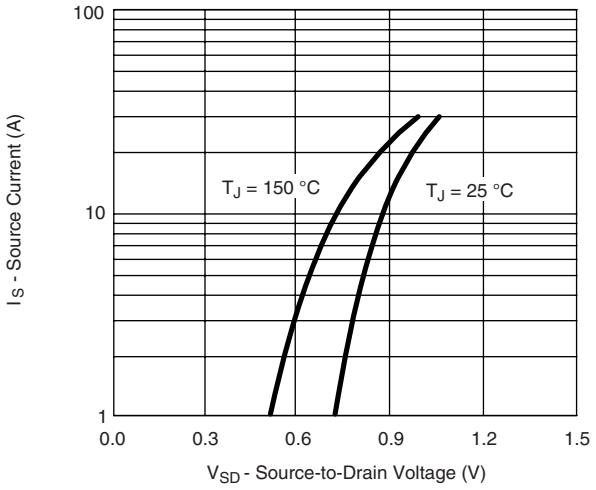


Gate Charge

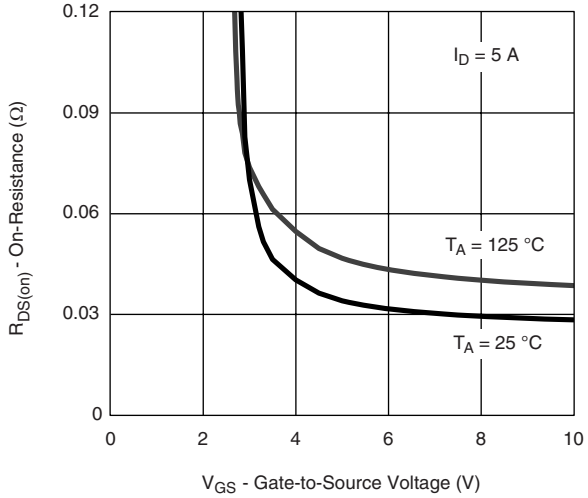


On-Resistance vs. Junction Temperature

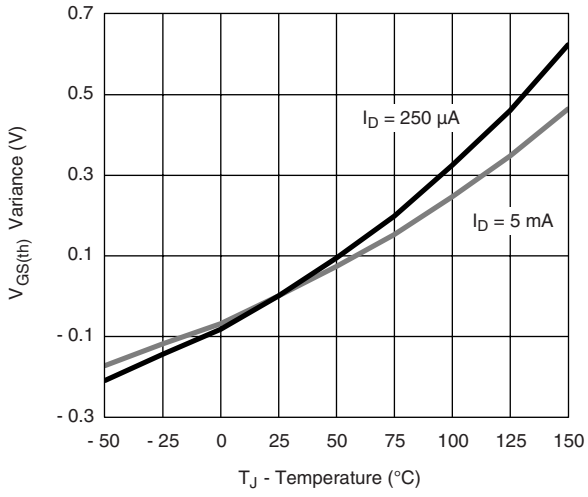
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



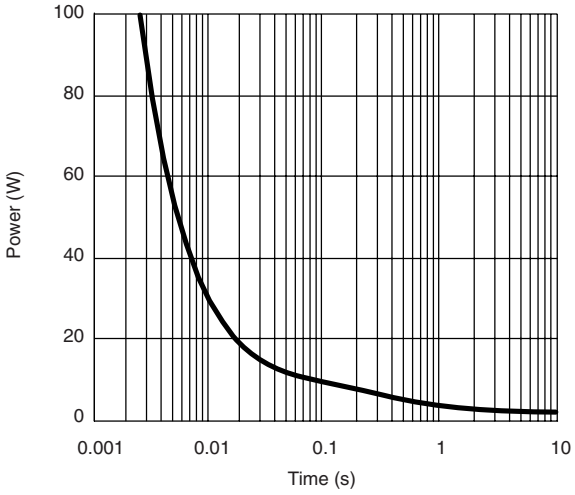
Source-Drain Diode Forward Voltage



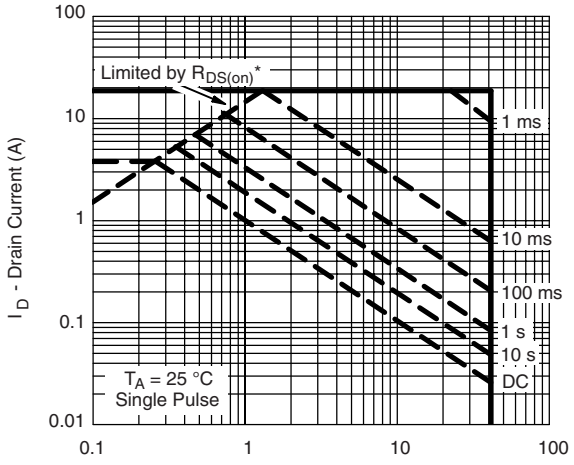
On-Resistance vs. Gate-to-Source Voltage



Threshold Voltage



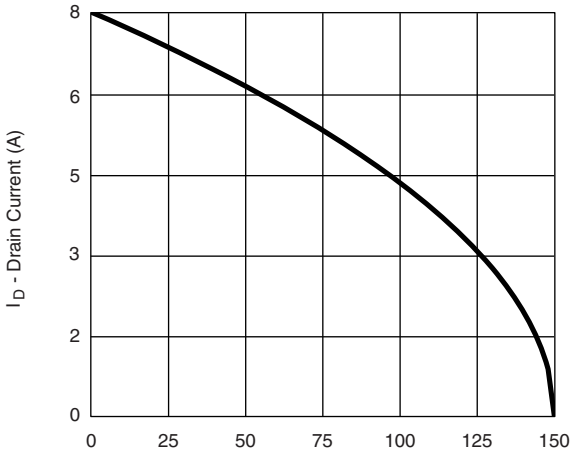
Single Pulse Power, Junction-to-Ambient



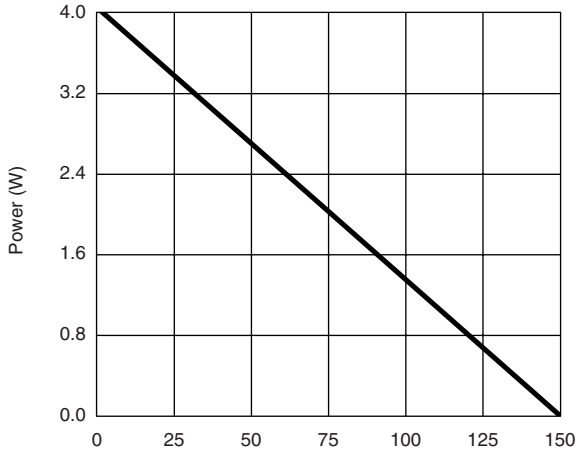
* V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

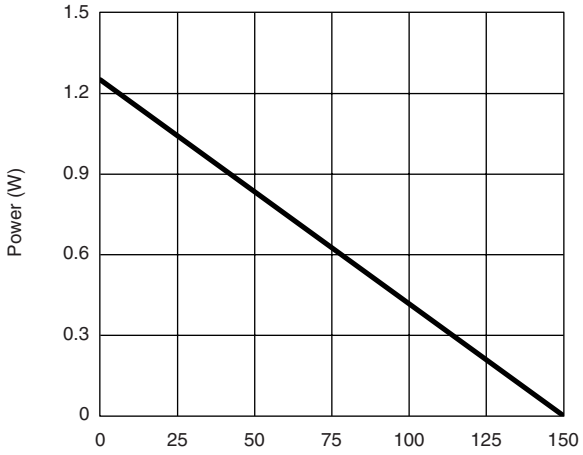
P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Current Derating*



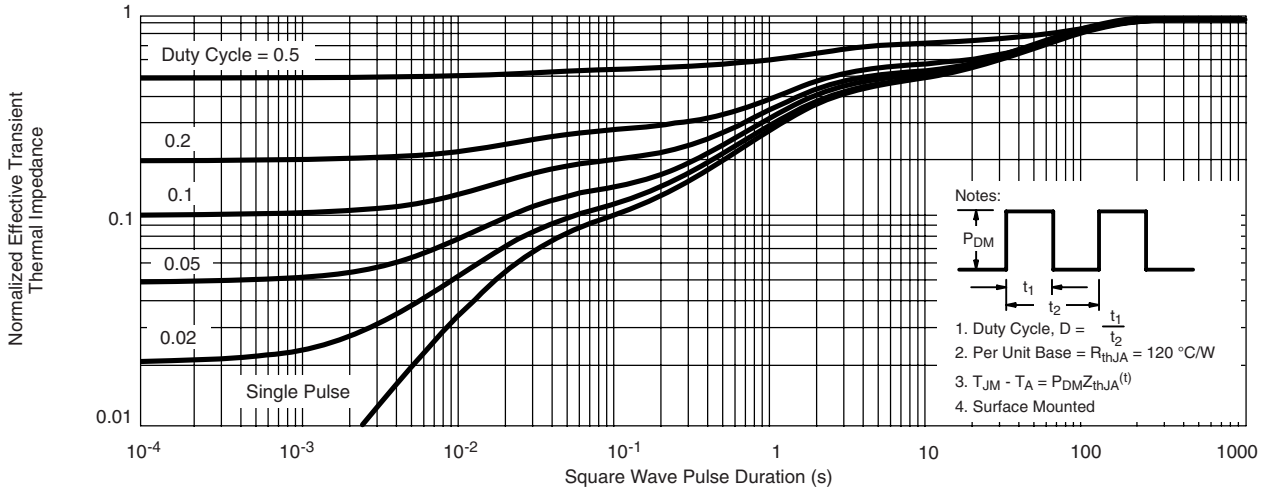
Power Derating, Junction-to-Foot



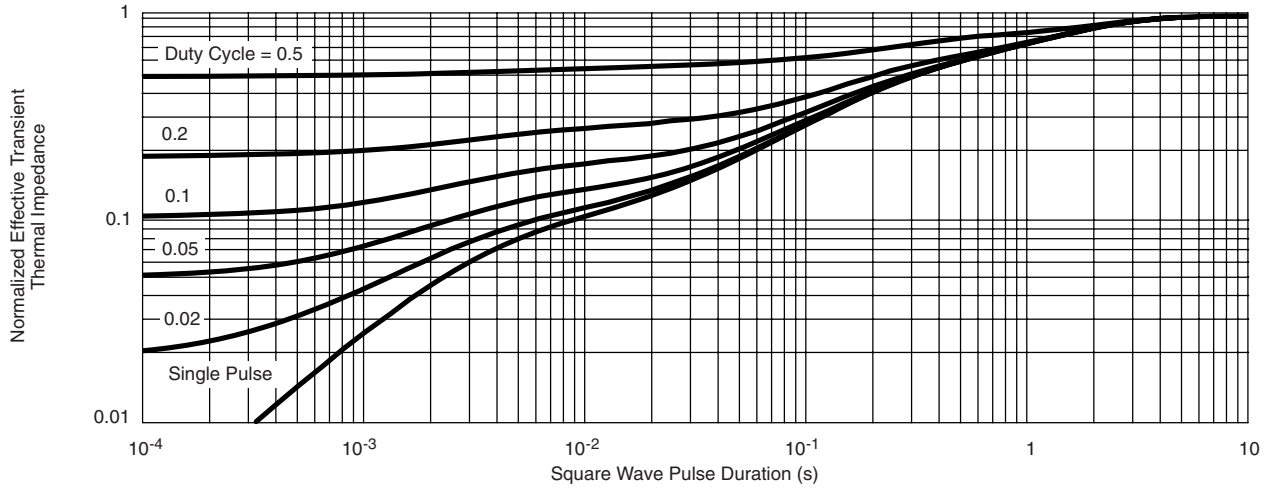
Power Derating, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)}$ = 150 °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

P-CHANNEL TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?69730.

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, “Vishay”), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay’s knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer’s responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer’s technical experts. Product specifications do not expand or otherwise modify Vishay’s terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.